

Standard Rectifier

=2x1600 V

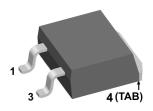
10 A

1.21 V

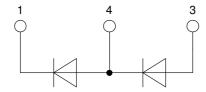
Phase leg

Part number

DMA10P1600PZ



Backside: anode/cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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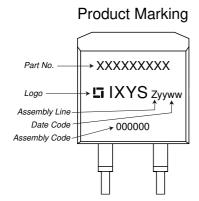


Rectifier					Ratings	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1700	٧
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1600	V
I _R	reverse current	V _R = 1600 V	$T_{VJ} = 25^{\circ}C$			10	μΑ
		$V_R = 1600 \text{ V}$	$T_{VJ} = 150$ °C			0.2	mΑ
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			1.26	V
		$I_F = 20 \text{ A}$				1.53	٧
		I _F = 10 A	$T_{VJ} = 150 ^{\circ}\text{C}$			1.21	٧
		$I_F = 20 A$				1.57	V
I _{FAV}	average forward current	T _C = 150°C	$T_{VJ} = 175$ °C			10	Α
		rectangular d = 0.5					i
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.82	٧
r _F	slope resistance \(\) for power	loss calculation only				37	mΩ
R _{thJC}	thermal resistance junction to ca	ase				1.5	K/W
R _{thCH}	thermal resistance case to heats	sink			0.25		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			100	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			120	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			130	Α
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			100	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			110	Α
I²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			72	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			70	A²s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			50	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			50	A²s
C	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		4		pF





Package TO-263 (D2Pak-HV)				Ratings			
Symbol	Definition Condition	ons	min.	typ.	max.	Unit	
I _{RMS}	RMS current per termi	nal			25	Α	
T _{VJ}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature				150	°C	
Weight				1.5		g	
F _c	mounting force with clip		20		60	N	
d _{Spp/App}	creepage distance on surface striking distance throu	terminal to terminal	4.2			mm	
d _{Spb/Apb}	creepage distance on surface striking distance tinot	terminal to backside	4.7			mm	



Part description

D = Diode

M = Standard Rectifier

A = (up to 1800V)

10 = Current Rating [A]

P = Phase leg

1600 = Reverse Voltage [V]

PZ = TO-263AB (D2Pak) (2HV)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA10P1600PZ	DMA10P1600PZ	Tape & Reel	800	513688

Similar Part	Package	Voltage class
DMA10P1800PZ	TO-263AB (D2Pak) (2HV)	1800
DAA10P1800PZ	TO-263AB (D2Pak) (2HV)	1800

Equiva	alent Circuits for	Simulation	* on die level	T _{VJ} = 175 °C
$I \rightarrow V_0$)— <u>R</u> o	Rectifier		
V _{0 max}	threshold voltage	0.82		V
$R_{0 \text{ max}}$	slope resistance *	34		$m\Omega$

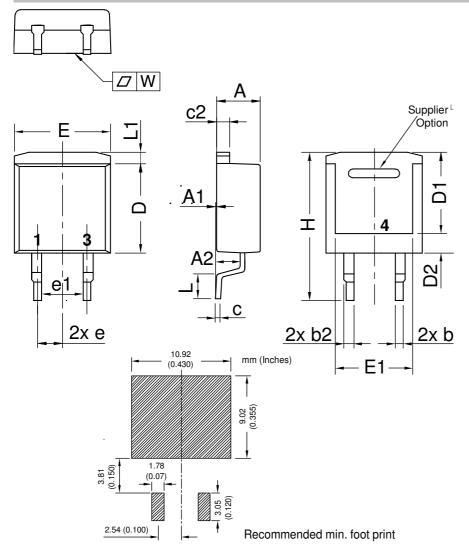
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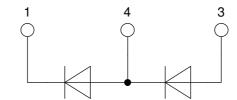


Outlines TO-263 (D2Pak-HV)



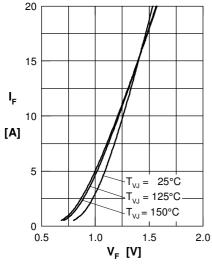
Dim.	Millir	neter	Inc	hes
DIIII.	min	max	min	max
Α	4.06	4.83	0.160	0.190
A1	typ.	0.10	typ. 0	0.004
A2	2.	41	0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
С	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2	.3	0.091	
Е	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
е	2,54	BSC	0,100 BSC	
e1	4.28		0.169	
Н	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

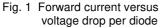
All dimensions conform with and/or within JEDEC standard.





Rectifier





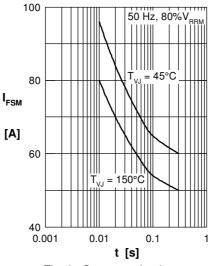


Fig. 2 Surge overload current

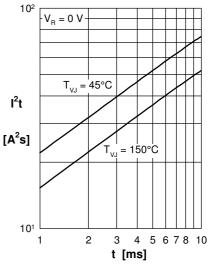


Fig. 3 I²t versus time per diode

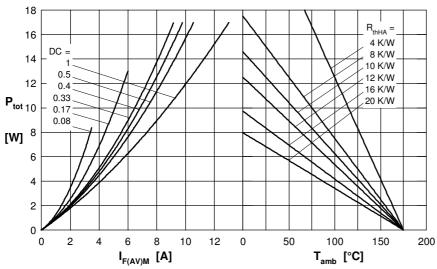


Fig. 4 Power dissipation vs. direct output current and ambient temperature

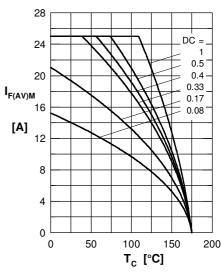


Fig. 5 Max. forward current vs. case temperature

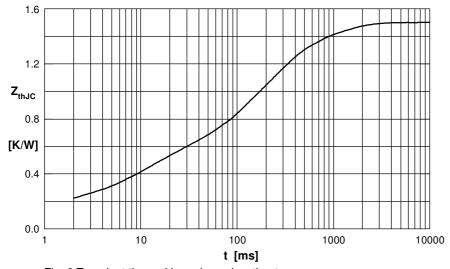


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	8.0

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